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(71) Applicant *(for all designated States except US)*: **MICRON TECHNOLOGY, INC.** [US/US]; 8000 S. Federal Way, Boise, ID 83707-0006 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **RHODES, Howard, E.** [US/US]; 631 E. Ridgefield Drive, Boise, ID 83706 (US). **MOULI, Chandra** [US/US]; 727 South Granite Way, Boise, ID 83712 (US).

(74) Agent: **D'AMICO, Thomas, J.**; Dickstein Shapiro Morin & Oshinsky LLP, 2101 L Street NW, Washington, DC 20037-1526 (US).

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(54) Title: ANGLED IMPLANT FOR TRENCH ISOLATION

(57) Abstract: A trench isolation having a sidewall and bottom implanted region located within a substrate of a first conductivity type is disclosed. The sidewall and bottom implanted region is formed by an angled implant, a 90 degree implant, or a combination of an angled implant and a 90 degree implant, of dopants of the first conductivity type. The sidewall and bottom implanted region located adjacent the trench isolation reduces surface leakage and dark current.